



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

#5  
Election/A  
DSmalls-Logan  
9-3-02

Applicants: Cher Huan TAN et al.  
Serial No.: 10/025,085  
Filed: December 19, 2001  
For: Method For Preventing  
Photoresist Poisoning In  
Semiconductor Fabrication

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§ Group Art Unit: 2813  
§  
§ Examiner: T. S. Pham  
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**RESPONSE TO RESTRICTION REQUIREMENT DATED JULY 9, 2002**

Assistant Commissioner for Patents  
Washington, D.C. 20231

Att'y. Docket No. 2085-00600  
Client Ref. No. IME-P002US/fmk  
Date: August 7, 2002

Sir:

This paper is filed in response to the Restriction Requirement dated July 9, 2002. The Examiner is requested to enter the following amendments and consider the accompanying remarks. Reconsideration is respectfully requested.

**AMENDMENT**

**IN THE CLAIMS:**

Applicants hereby respectfully requests amendments to claims 1, 11, 12 and 16, by replacement with rewritten claims 1, 11, 12 and 16, as follows:

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- 1 1. (Once Amended) In a via-first dual damascene process involving the use of a low-K
- 2 dielectric material as an insulation layer on a wafer substrate during the fabrication of an integrated
- 3 circuit, a method for photolithographic patterning comprising the steps of:
- 4 filling an aperture etched into an insulation layer on a wafer substrate with a fill-in material
- 5 for isolating the insulation layer from photoresist deposited thereafter;